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I hereby certify that this paper (along with any referred to as being attached or enclosed) is being deposited with the United States Postal Service on September 17, 2002 with sufficient postage as first class mail in an envelope addressed: Assistant Commissioner for Patents, Washington, D.C. 20231.

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**PATENT**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Serial No.: 10/080,496  
Filed: February 22, 2002  
Applicant: Jozef Brcka  
Art Unit: 1741  
Title: MODIFIED TRANSFER FUNCTION DEPOSITION BAFFLES AND HIGH DENSITY PLASMA IGNITION THEREWITH IN SEMICONDUCTOR PROCESSING  
Attorney Docket: TAZ-213

Cincinnati, OH 45202

September 17, 2002

Assistant Commissioner for Patents  
Washington, D.C. 20231

**PRELIMINARY AMENDMENT**

In the Specification

Replace paragraph numbers [0004], [0006], [0007], [0012], [0014] and [0064], with the following amended paragraphs:

**[0004]** This invention relates to inductively-coupled plasma (ICP) sources used in the processing of semiconductors. The invention is particularly applicable to high-density inductively-coupled plasma (HDICP) sources in which RF energy is inductively coupled through a dielectric material that is protected by a slotted deposition baffle to energize a plasma for depositing an electrically conductive material onto, or etching an electrically conductive material from, a semiconductor wafer.

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02 FC:102

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Page 1 of 14